

600V/800A HALF BRIDGE PEM

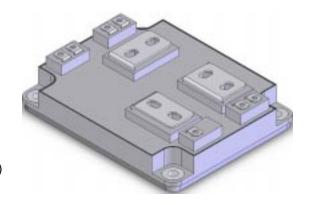
4802

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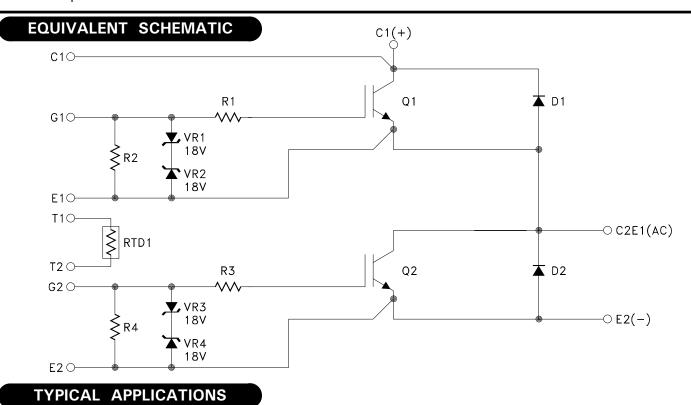
FEATURES:

- · Half Bridge Configuration
- 600V Rated Voltage
- 800A Continuous Output Current
- Internal Zener Clamps on Gates; Internal RTD
- Proprietary Encapsulation Provides Near Hermetic Performance
- MIL-PRF-38534 Screening Available (Modified)
- · Light Weight Domed ALSIC Baseplate
- Robust Mechanical Design for Hi-Rel Applications
- · Ultra-Low Inductance Internal Layout
- Withstands 96 Hours HAST and Thermal Cycling (-55°C to +125°C)
- · High Side Collector Sense Pin for De-Sat Detection



DESCRIPTION:

The MSK 4802 is one of a family of plastic encapsulated modules (PEM) developed specifically for use in military, aerospace and other severe environment applications. The half bridge configuration and 600 volt/800 amp rating make it ideal for use in high current motor drive and inverter applications. The Aluminum Silicon Carbide (AlSiC) baseplate offers superior flatness and light weight; far better than the copper or copper alloys found in most high power plastic modules. The high thermal conductivity materials used to construct the MSK 4802 allow high power outputs at elevated baseplate temperatures. Our proprietary coating, SEES™ - Severe Environment Encapsulation System - protects the internal circuitry of MSK PEM's from moisture and contamination, allowing them to pass the rugged environmental screening requirements of military and aerospace applications. MSK PEM's are also available with industry standard silicone gel coatings for a lower cost option.



- Motor Drives
- Inverters

ABSOLUTE MAXIMUM RATING



VCE	Collector to Emitter Voltage	. 600V	Tst	Storage Temperature Range55 °C to +125 °	С
Vge	Gate to Emitter Voltage	±20V	TJ	Junction Temperature	C
lout	Current (Continuous)	800A	Tc	Case Operating Temperature Range	
IOUTP	Current Pulsed (1mS)	1000A		MSK 4802H/E55°C to +125°	С
VCASE	Case Isolation Voltage	500 V		MSK 480240°C to +85°	С

ELECTRICAL SPECIFICATIONS

Parameter (6)		Test Conditions		Group A	MSK 4800 H/E		MSK 4800			Units	
			Subgroup	Min.	Typ.	Max.	Min.	Тур.	Max.		
				1	1094	TBD	1098.5	1094	TBD	1098.5	Ω
RTD Resistance		VCE = OV, VGE = OV, IC = OA		2	1476	TBD	1486	1476	TBD	1486	Ω
				3	785	TBD	791	785	TBD	791	Ω
				1	-	TBD	2.5	-	TBD	2.6	V
	IC = 800A, VGE = 15V		'GE = 15V	2	-	TBD	2.7	-	TBD	2.8	V
Collector-Emitter Saturati			3	-	TBD	2.6	-	TBD	2.7	V	
Collector-Emitter Saturati	ion voltage	· · · · · · · · · · · · · · · · · · ·		1	-	TBD	1.9	-	TBD	2.0	V
		IC = 400A, VGE = 15V		2	-	TBD	2.1	-	TBD	2.2	V
				3	-	TBD	2.1	-	TBD	2.2	V
				1	1	TBD 2.0 - TBD		5.0	mΑ		
Collector-Emitter Leakage	e Current	VCE = 600V, VGE = 0V		2	-	TBD	18	-	TBD	18	mA
				① 3	1	TBD	2.0	-	TBD	5.0	mΑ
		IC = 100mA, VCE = 10V		1	4.0	TBD	7.5	-	TBD	7.9	V
Gate Threshold Voltage				2	4.0	TBD	7.5	-	TBD	7.9	٧
				3	4.0	TBD	8.5	-	TBD	8.9	V
		IC = 800A		1	-	TBD	2.5	-	TBD	2.6	V
				2	-	TBD	2.1	-	TBD	2.2	V
Diode Forward Voltage	Favorard Valence				-	TBD	2.8	-	TBD	2.9	V
Diode i orward voltage		IC = 400A		1	ı	TBD	2.0	-	TBD	2.1	V
				2	-	TBD	1.9	-	TBD	2.0	V
				3	1	TBD	2.3	-	TBD	2.4	>
Total Gate Charge ① Low Side Only	VCC = 35	50V, IC=800A,	VGE+15V/-7V	4	-	TBD	6500	-	TBD	6500	nC
			IC = 800A	4	-	TBD	40	-	TBD	40	mJ
Eon (1)	(1)		IC = 400A	4	-	TBD	30	-	TBD	30	mJ
EOII (I)			IC = 800A	-	-	TBD	-	-	TBD	-	mJ
Low Side Only	e Only		IC = 400A	5	-	TBD	-	-	TBD	-	mJ
			IC = 800A	4	-	TBD	60	-	TBD	60	mJ
Eoff (1)	1)		IC = 400A	4	-	TBD	30	-	TBD	30	mJ
E011 (1)			IC = 800A	5	-	TBD	-	-	TBD	-	mJ
Low Side Only			IC = 400A	J	-	TBD	-	-	TBD	-	mJ
Erec (1)	VCC = 350	V, RG = 2.5Ω	IC = 800A	4	-	TBD	7	-	TBD	7	mJ
Low Side Only	VGE = +	15V/-7V	IC = 400A	4	-	TBD	6	-	TBD	6	mJ
Thermal Resistance (1)	esistance ①			4		TBD	0.045	-	TBD	0.045	°C/W
mermai nesistance ()			4	-	TBD	0.075	-	TBD	0.075	°C/W	

NOTES:

- ① Guaranteed by design but not tested. Typical parameters are representative of actual device performance but are for reference only.
 ② Industrial grade and "E" suffix devices shall be tested to subgroup 1 unless otherwise specified.
 ③ Military grade devices ("H" suffix) shall be 100% tested to subgroups 1, 2 and sample tested to subgroup 3.
 ④ Subgroup 4 testing available upon request.
 ⑤ Subgroup 1, 4 TA = +25°C
 2, 5 TA = +125°C
 3 6 Th = 550°C

- - 3, 6 TA = -55° C
- © Unless otherwise specified all specifications apply to both the upper and lower sections of the half bridge. Toolinuous operation at or above absolute maximum ratings may adversly effect the device performance a Continuous operation at or above absolute maximum ratings may adversly effect the device performance and/or life cycle

APPLICATION NOTES

THERMAL CALCULATIONS

Power dissipation and maximum allowable temperature rise involve many variables working together. Collector current, PWM duty cycle and switching frequency all factor into power dissipation. DC losses or "ON-TIME" losses are simply VCE(SAT) x Collector Current x PWM duty cycle. For the MSK 4802, VCE(SAT) = TBDV max., and at 800 amps and a PWM duty cycle of 30%, DC losses equal TBD watts. Switching losses vary proportionally with switching frequency. The MSK 4802 typical switching losses at VCE = 300V and ICE = 800A are about TBDmJ, which is simply the sum of the turn-on switching loss and the turn-off switching loss. Multiplying the switching frequency times the switching losses will result in a power dissipation number for switching. The MSK 4802, at 5KHz, will exhibit switching power dissipation of TBD watts. The total losses are the sum of DC losses plus switching losses, or in this case, TBD watts total.

TBD watts x TBD°C/W thermal resistance equals TBD degrees of temperature rise between the case and the junction. Subtracting TBD°C from the maximum junction temperature of 150°C equals TBD°C maximum case temperature for this example.

VCE(SAT) x IC x PWM duty cycle = TBDV x 800 amps x 30% = TBD watts DC losses

Turn-on switching loss + Turn-off switching loss = Total switching losses = TBD + TBD = TBDmJ

Total switching loss x PWM frequency = Total switching power dissipation = TBDmJ x 5KHz = TBD watts

Total power dissipation = DC losses + switching losses = TBD + TBD = TBD watts

Junction temperature rise above case = Total power dissipation x thermal resistance

TBD watts x TBD $^{\circ}$ C/W = TBD $^{\circ}$ C temperature rise above case

Maximum junction temperature - junction temperature rise = maximum baseplate temperature

 $150^{\circ}\text{C} - \text{TBD}^{\circ}\text{C} = \text{TBD}^{\circ}\text{C}$

TYPICAL PERFORMANCE CURVES

TBD

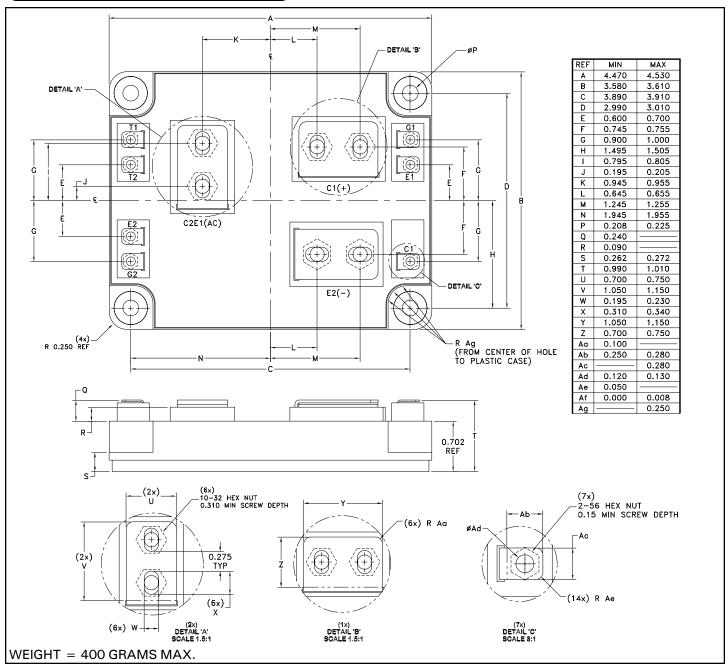
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SCREENING CHART

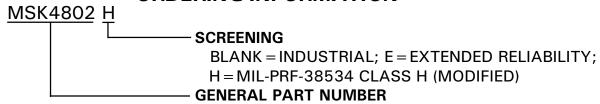
OPERATION IN ACCORDANCE WITH MIL-PRF-38534	INDUSTRIAL	CLASS E	CLASS H
QUALIFICATION (MODIFIED)	NO	NO	YE\$
ELEMENT EVALUATION	NO	YES	YES
CLEAN ROOM PROCESSING	YES	YES	YES
NON DESTRUCT BOND PULL SAMPLE	YES	YES	YES
CERTIFIED OPERATORS	NO	YES	YES
MIL LINE PROCESSING	YES	YES	YES
MAX REWORK SPECIFIED	NO	YES	YES
ENCAPSULANT	GEL COAT	SEES ™	SEES TM
PRE-CAP VISUAL	YES - INDUSTRIAL	YES - CLASS H	YES - CLASS H
TEMP CYCLE (-55°C TO +125°C)	NO	YES	YES
BURN-IN	NO	YES - 96 HOURS	YES - 160 HOURS
ELECTRICAL TESTING	YES - 25°C	YES - 25°C	YES - FULL TEMP
EXTERNAL VISUAL	YES - SAMPLE	YES - SAMPLE	YES
XRAY	NO	NO	NO
PIN FINISH	NI	NI	NI

NOTE: ADDITIONAL SCREENING IS AVAILABLE SUCH AS XRAY, CSAM, MECHANICAL SHOCK, ETC. CONTACT FACTORY FOR QUAL STATUS.

MECHANICAL SPECIFICATIONS



ORDERING INFORMATION



THE ABOVE EXAMPLE IS A MILITARY SCREENED MODULE.

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